	Application No.	Applicant(s)	
Notice of Allowability	10/800,190	HASELDEN ET AL.	
	Examiner	Art Unit	
	Lisa Kilday	2829	
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comming IGHTS. This application is	in this application. If not included nunication will be mailed in due co	ourse. THIS
1. A This communication is responsive to 3/12/4.			
2. ⊠ The allowed claim(s) is/are <u>1-11</u> .			
3. $igotimes$ The drawings filed on <u>12 March 2004</u> are accepted by the	Examiner.		
4. Acknowledgment is made of a claim for foreign priority uner a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be subminsFORMAL PATENT APPLICATION (PTO-152) which give (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the deposit of the depo	e been received. e been received in Application cuments have been received of this communication to fill MENT of this application. Initiated. Note the attached EXes reason(s) why the oath of the submitted. Son's Patent Drawing Reviews Amendment / Comment of the header according to 37 Consit of BIOLOGICAL MATERIAL COMMENT.	on No ed in this national stage application e a reply complying with the requestamine as a reply complying with the requestamine and the control of the drawings in the front (not the best of the drawings in the submitted. No	irements TICE OF
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 3/4) 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview 9 Paper No 08), 7. ☑ Examiner's	nformal Patent Application (PTO- Summary (PTO-413), ./Mail Dates s Amendment/Comment s Statement of Reasons for Allow 	

EXAMINER'S AMENDMENT

An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with David Park on 9/1/04.

The application has been amended as follows:

Amend the following claims 4 and 9.

Claim 4: change "20:1" to --15:1--.

Claim 9: after, "is between", insert --greater than--.

The reasons for the examiner's amendment are to clarify the overlapping ranges of the flowrate ratios between 15:1 and 20:1. If the claims contained overlapping ranges, any flowrate ratios falling between 15:1 – 20:1 would read on the instant claims because only one teaching would be necessary to overcome the shared first and second flowrate ratios. This amendment is supported by the values found in Table I of the instant specification.

The following is an examiner's statement of reasons for allowance: In re claims 1-10, Chien et al. (5,643,824) teaches in figs. 1-2 a method of manufacturing a gate structure over a substrate comprising: providing a Silicon oxide layer (12); providing a Silicon nitride layer (16) over the Silicon oxide layer, providing a first gas flow including a first gas flow having a first ratio of fluorine to carbon atoms (col. 4, lines 55-57);

applying a plasma to said first gas flow to create a first plasma and etching a first portion of said Silicon nitride with said first plasma (col. 4, lines 63-65). However, prior art does not teach or suggest a second gas flow including a second ratio of fluorine atoms to carbon atoms where the second ratio is greater than said first ratio to form the Silicon nitride spacer.

In re claim 11, Chien et al. (5,643,824) teaches in figs. 1-2 a method of manufacturing a gate structure over a substrate comprising: providing a Silicon oxide layer (12); providing a Silicon nitride layer (16) over the Silicon oxide layer, providing a first gas flow of CF4 (col. 4, line 43) to CHF3 flow rate (col. 4, lines 55-57); applying a plasma to said first gas flow to create a first plasma and etching a first portion of said Silicon nitride with said first plasma (col. 4, lines 63-65). However, prior art does not teach or suggest including the limitation of *CH2F2* as part of the first gas flow. Nor does prior art teach or suggest the limitations above combined with: a second gas flow including a second ratio of CF4 to CH2F2 where the second ratio is greater than said first ratio to form the Silicon nitride spacer.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry of a general nature or relating to the status of this application should be directed to the Group Receptionist whose telephone number is (703) 308-0957. See MPEP 203.08.

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Any inquiry concerning this communication from the examiner should be directed to Lisa Kilday whose telephone number is (571) 272-1962. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Tokar, can be reached on (571) 272-1812. The fax number for the group is (703) 872-9306. MPEP 502.01 contains instructions regarding procedures used in submitting responses by facsimile transmission.

Lisa Kilday

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9/2/04

Michael Tokar Supervisory Patent Examiner Technology Center 2800

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